

## **Metal Assisted Chemical Etching for Silicon Nanowires Formation**

In this work the silicon nanopillars were produced by means of metal assisted chemical etching in two stages. It was determined that using the amount of  $\text{AgNO}_3$  of 68 mg in the first solution and the duration of the first stage of 20 sec made possible to reduce the sunlight reflection of silicon substrate from 20-30% to 10-12%.

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